



General Description

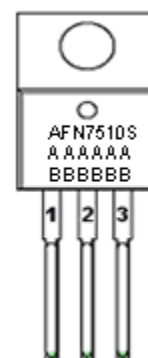
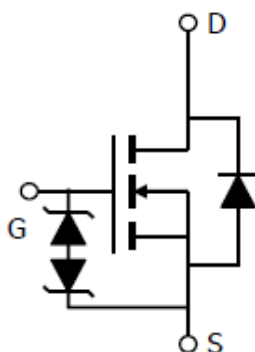
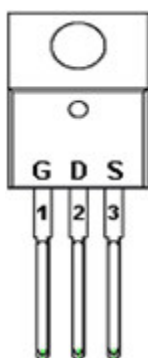
AFN7510S, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

- 100V/30A, $R_{DS(ON)} = 12m\Omega @ V_{GS} = 10V$
- 100V/15A, $R_{DS(ON)} = 18m\Omega @ V_{GS} = 6V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- TO-220-3L package design

Pin Description (TO-220-3L)



Application

- DC/DC Primary Side Switch
- POL Synchronous buck converter
- LED Backlight for LCD TV industrial

Pin Define

Pin	Symbol	Description
1	G	Gate
2	D	Drain
3	S	Source

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN7510ST220TG	AFN7510S AAAAAA BBBBBB	TO-220-3L	Tube	50 EA

- ※ A Lot code
- ※ B Date code
- ※ AFN7510ST220TG : Tube ; Pb- Free ; Halogen- Free



Absolute Maximum Ratings

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	100	V
Gate –Source Voltage	V _{GSS}	±20	V
Continuous Drain Current(T _J =150°C)	I _D	T _C =25°C	60
		T _C =70°C	35
Pulsed Drain Current	I _{DM}	130	A
Continuous Source Current(Diode Conduction)	I _S	70	
Single Pulse Avalanche Current	I _{AS}	20	
Power Dissipation	P _D	75	W
Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	62.5	°C/W

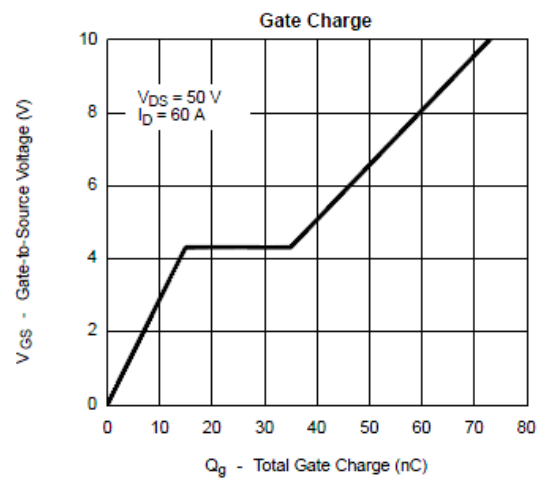
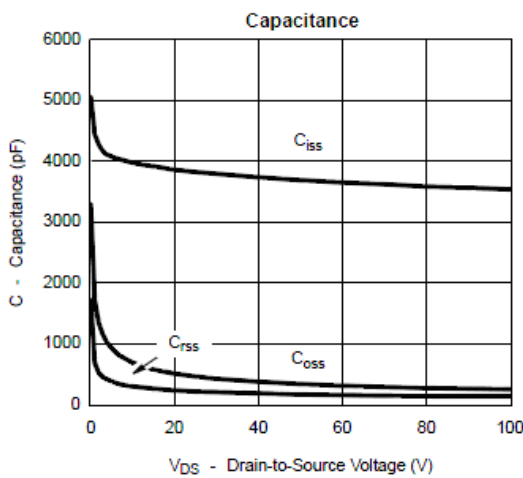
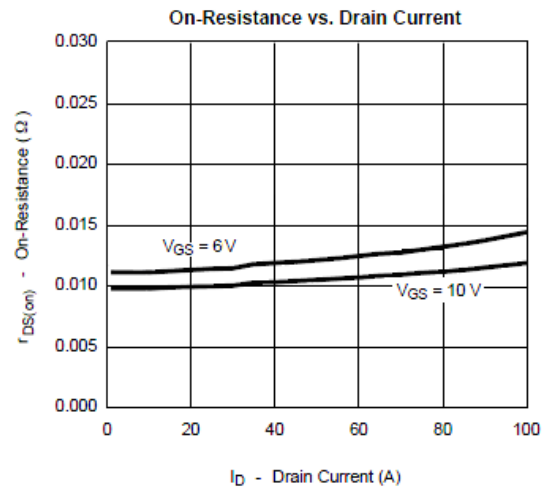
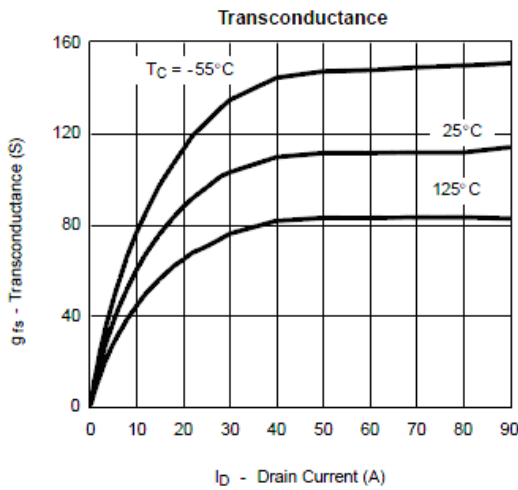
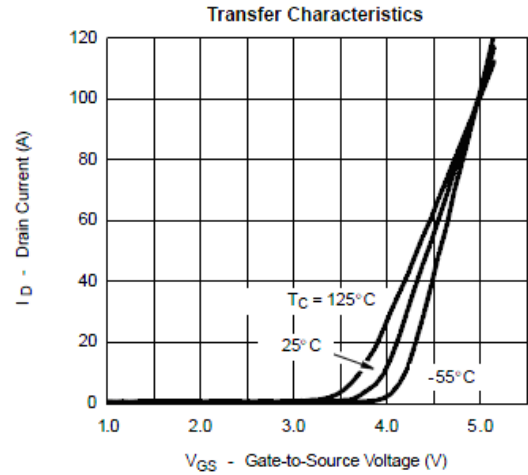
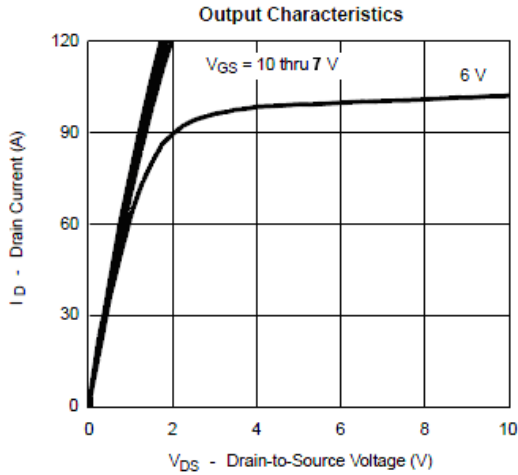
Electrical Characteristics

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250uA	100			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	2.0		4.0	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±5	uA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =80V, V _{GS} =0V			1	uA
		V _{DS} =80V, V _{GS} =0V T _J =85°C			30	
On-State Drain Current	I _{D(on)}	V _{DS} ≥ 10V, V _{GS} =10V	130			A
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =30A		9.5	12	mΩ
		V _{GS} =6V, I _D =15A		12.4	18	
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =20A		30		S
Diode Forward Voltage	V _{SD}	I _S =20A, V _{GS} =0V		0.8	1.3	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =50V, V _{GS} =10V I _D ≡60A		75	150	nC
Gate-Source Charge	Q _{gs}			15		
Gate-Drain Charge	Q _{gd}			20		
Input Capacitance	C _{iss}	V _{DS} =40V, V _{GS} =0V f=1MHz		3800		pF
Output Capacitance	C _{oss}			450		
Reverse Transfer Capacitance	C _{rss}			210		
Turn-On Time	t _{d(on)}	V _{DD} =50V, R _L =0.8Ω I _D ≡60A, V _{GEN} =10V R _G =2.5Ω		15	30	ns
	t _r			80	150	
Turn-Off Time	t _{d(off)}			50	100	
	t _f			130	250	

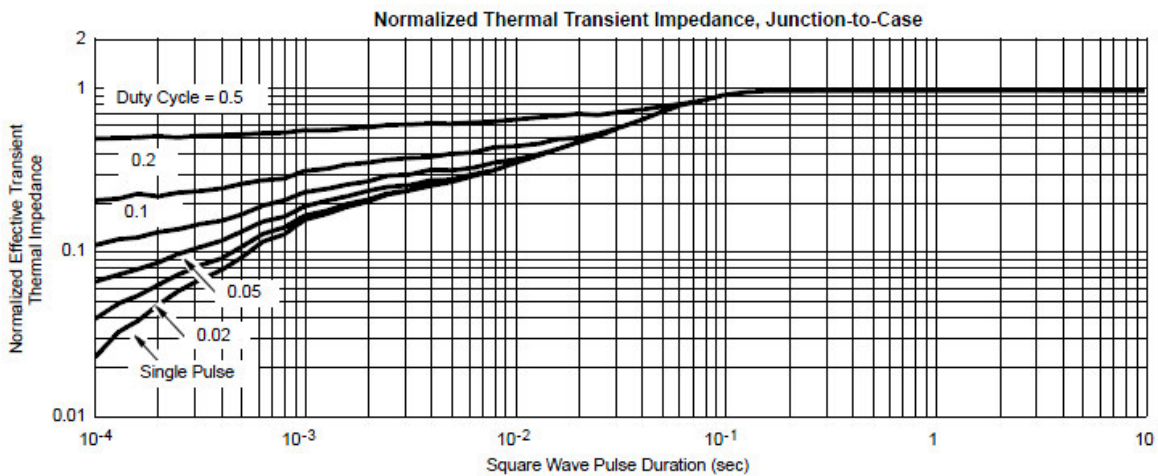
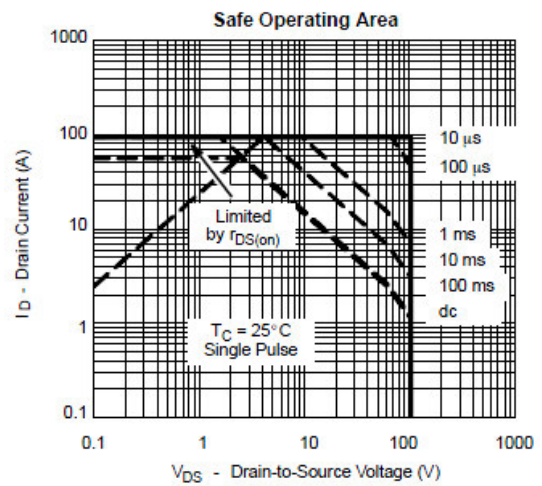
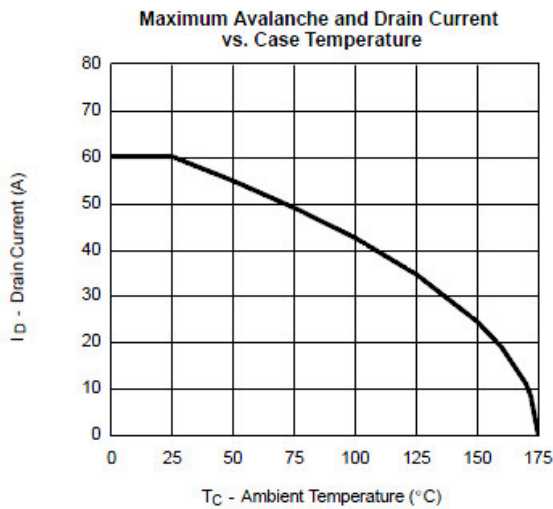
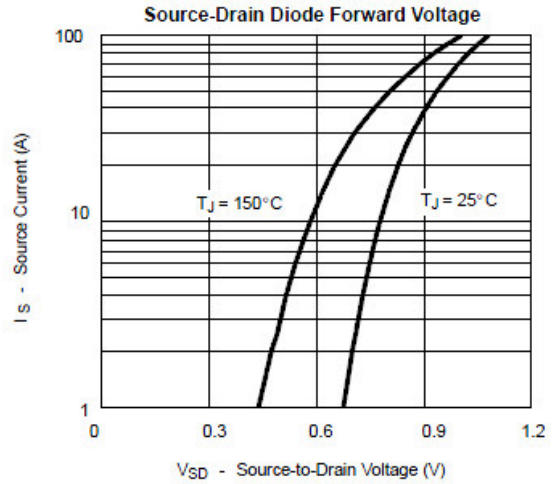
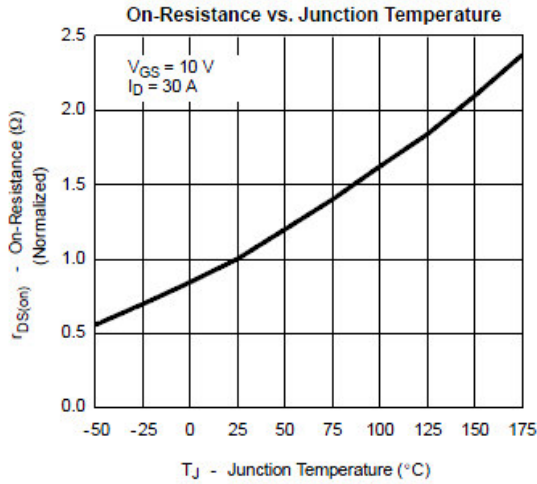


Typical Characteristics





Typical Characteristics





Typical Characteristics

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

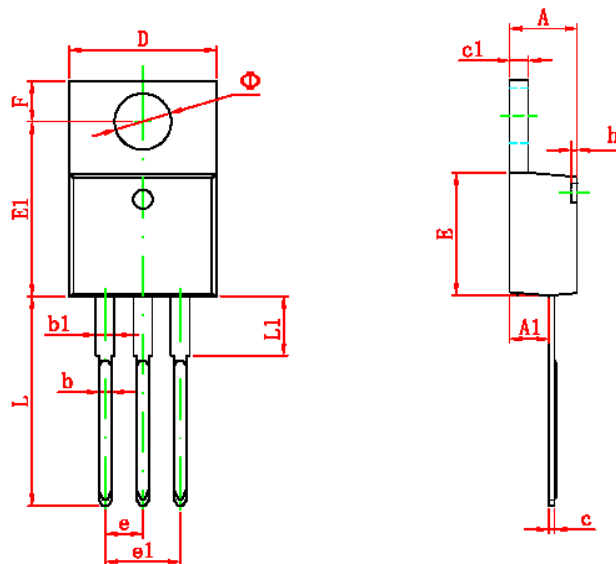


Unclamped Inductive Switching Test Circuit & Waveforms





Package Information (TO-220-3L)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.470	4.670	0.176	0.184
A1	2.520	2.820	0.099	0.111
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
E1	12.060	12.460	0.475	0.491
e	2.540 TYP		0.100 TYP	
e1	4.980	5.180	0.196	0.204
F	2.590	2.890	0.102	0.114
h	0.000	0.300	0.000	0.012
L	13.400	13.800	0.528	0.543
L1	3.560	3.960	0.140	0.156
• •	3.735	3.935	0.147	0.155

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